

Application No. 10/700,429  
Reply to Office Action of July 11, 2005  
Amendment dated January 11, 2006

Amendments to the Specification

*insec4*

*year 1/21/2010*

Please ~~replace the paragraph that was inserted~~  
before the first line of the specification with the following *Yn*  
~~amended version of that paragraph:~~

This application is a continuation of copending, commonly assigned United States Patent Application No. 09/775,597, filed February 5, 2001, now U.S. Patent No. 6,682,981, which is a continuation of United States Patent Application No. 09/027,959, filed February 23, 1998, now abandoned, which is a division of United States Patent Application No. 08/850,749, filed May 2, 1997, now U.S. Patent No. 5,985,693, which is a continuation of United States Patent Application No. 08/315,905, filed September 30, 1994, now U.S. Patent No. 5,869,354, which is a division of United States Patent Application No. 07/865,412, filed April 8, 1992, now U.S. Patent No. 5,354,695, all of which are incorporated by reference herein in their entireties.

Please replace the paragraph at page 24, lines 10-34 with the following amended version of that paragraph:

The Air Tunnel structure in one embodiment is fabricated with CVD processing techniques; alternatively, ECR (Electron-Cyclotron-Resonance) plasma CVD processing may soon provide an alternative deposition method. The gaseous dielectric separation of a conductor or a semiconductor device is accomplished by forming a sacrificial CVD film of a-Si, polysilicon or alternate material (typically dielectric material) that can be deposited by CVD means and selectively etched versus the other MDI circuit membrane material layers.